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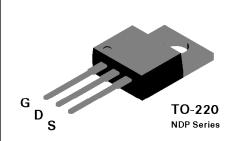
NDP6060 / NDB6060 N-Channel Enhancement Mode Field Effect Transistor

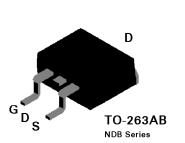
General Description

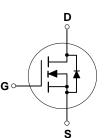
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as automotive, DC/DC converters, PWM motor controls, and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

- 48A, 60V. $R_{DS(ON)} = 0.025\Omega @ V_{GS} = 10V.$
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- 175°C maximum junction temperature rating.
- High density cell design for extremely low R_{DS(ON)}.
- TO-220 and TO-263 (D²PAK) package for both through hole and surface mount applications.







Absolute Maximum Ratings T_c = 25°C unless otherwise noted

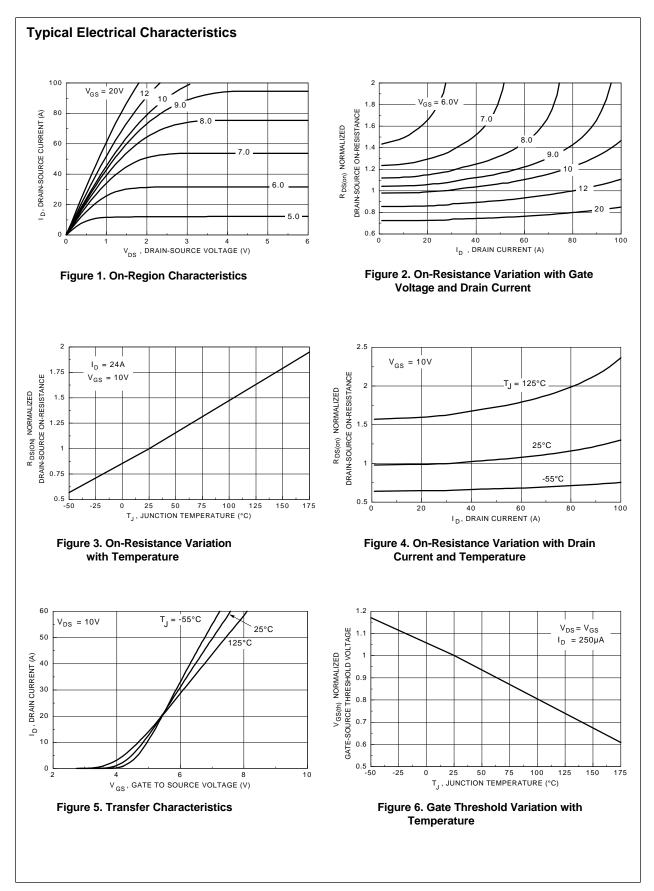
Symbol	Parameter	NDP6060	DP6060 NDB6060	
V _{DSS}	Drain-Source Voltage	60		
V_{DGR}	Drain-Gate Voltage ($R_{_{GS}} \le 1 \text{ M}\Omega$)	60		
V _{GSS}	Gate-Source Voltage - Continuous	±20		V
	- Nonrepetitive ($t_P < 50 \ \mu s$)	±40		
I _D	Drain Current - Continuous T _c =25°C	48		А
	- Continuous T _c =100°C	32		
	- Pulsed	144		
P _D	Total Power Dissipation @ $T_c = 25^{\circ}C$	100		
	Derate above 25°C	0.67	W/°C	
T_,,T _{stg}	Operating and Storage Temperature Range	-65 to 175		
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	275		°C

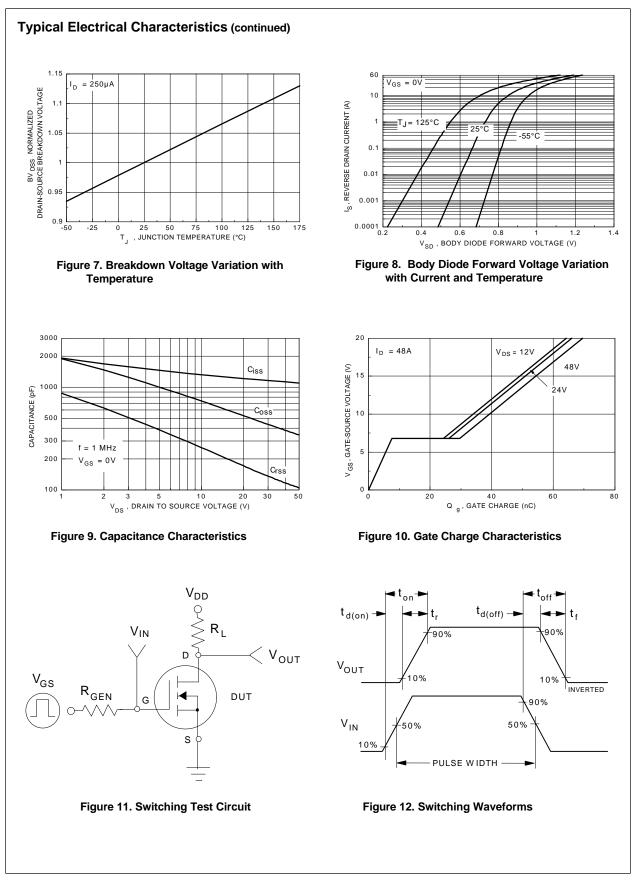
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Symbol	Parameter	Conditions		Min	Тур	Max	Units
DRAIN-SO	DURCE AVALANCHE RATINGS (Note 1)	•			•		
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 25 \text{ V}, \text{ I}_{D} = 48 \text{ A}$				200	mJ
I _{AR}	Maximum Drain-Source Avalanche Cur	rrent				48	Α
OFF CHA	RACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = 250 \mu A$		60			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{\rm DS} = 60 \text{ V}, V_{\rm GS} = 0 \text{ V}$				250	μA
			T _J = 125°C			1	mA
GSSF	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$	Ŀ			100	nA
	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$				-100	nA
ON CHAF	ACTERISTICS (Note 1)						
V _{GS(th)}	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}, \ I_{\text{D}} = 250 \ \mu\text{A}$		2	2.9	4	V
()			T _J = 125°C	1.4	2.3	3.6	
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 24 \text{ A}$ $T_{J} = 125^{\circ}\text{C}$	L.		0.02	0.025	Ω
				0.032	0.04		
D(on)	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 10 \text{ V}$	L.	48			А
9 _{FS}	Forward Transconductance	$V_{\rm DS} = 10 \text{ V}, I_{\rm D} = 24 \text{ A}$		10	19		S
DYNAMIC	CHARACTERISTICS						
C _{iss}	Input Capacitance	$V_{DS} = 25 V, V_{GS} = 0 V,$ f = 1.0 MHz			1190	1800	pF
C _{oss}	Output Capacitance				475	800	pF
C _{rss}	Reverse Transfer Capacitance				150	400	pF
SWITCHI	NG CHARACTERISTICS (Note 1)				•		
t _{D(on)}	Turn - On Delay Time	$V_{DD} = 30 \text{ V}, \text{ I}_{D} = 48 \text{ A},$ $V_{GS} = 10 \text{ V}, \text{ R}_{GEN} = 7.5 \Omega$			10	20	nS
t,	Tum - On Rise Time				145	300	nS
D(off)	Turn - Off Delay Time				28	60	nS
<u>,,</u>	Turn - Off Fall Time				77	150	nS
Q	Total Gate Charge	V _{DS} = 48 V,			39	70	nC
Q _{gs}	Gate-Source Charge	$I_{\rm D} = 48 \text{ A}, V_{\rm GS} = 10 \text{ V}$			7.6		nC
Q _{gd}	Gate-Drain Charge	1			22		nC

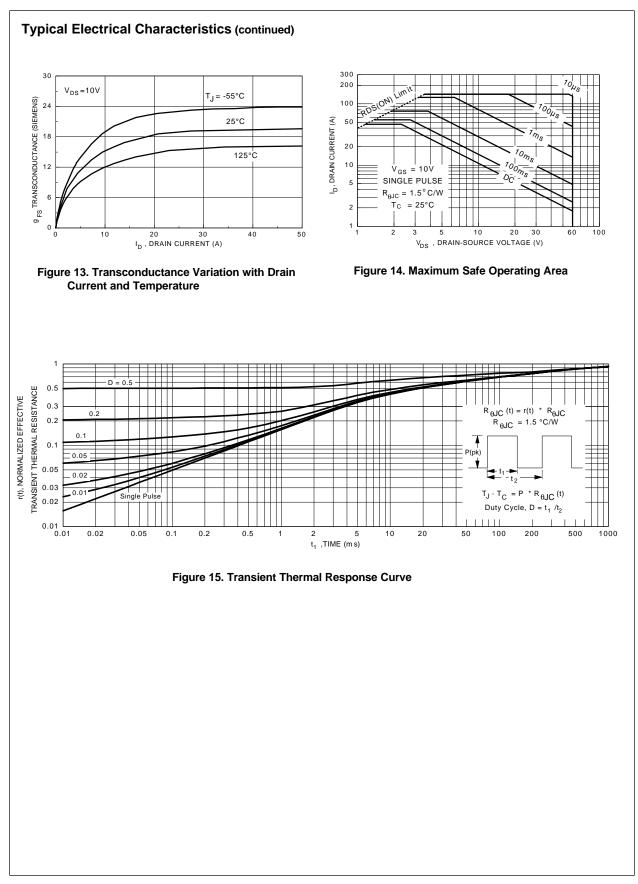
Electric	cal Characteristics (T _c = 25°C unle	ss otherwise noted)					
Symbol	Parameter	Conditions		Min	Тур	Max	Units
DRAIN-SO	OURCE DIODE CHARACTERISTICS	·					
l _s	Maximum Continuos Drain-Source Diode Forward Current				48	А	
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				144	А	
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_{S} = 24 A (Note 1)$			0.9	1.3	V
			T _J = 125°C		0.8	1.2	
t _m	Reverse Recovery Time	$V_{GS} = 0 V, I_F = 48 A,$ $dI_F/dt = 100 A/\mu s$		35	87	140	ns
l _{rr}	Reverse Recovery Current	$- \alpha_{\rm F}/\alpha_{\rm I} = 100 \text{Av}\mu\text{s}$		2	3.6	8	А
THERMA	CHARACTERISTICS	·					
R _{θJC}	Thermal Resistance, Junction-to-Case					1.5	°C/W
R _{ØJA}	Thermal Resistance, Junction-to-Ambient				62.5	°C/W	

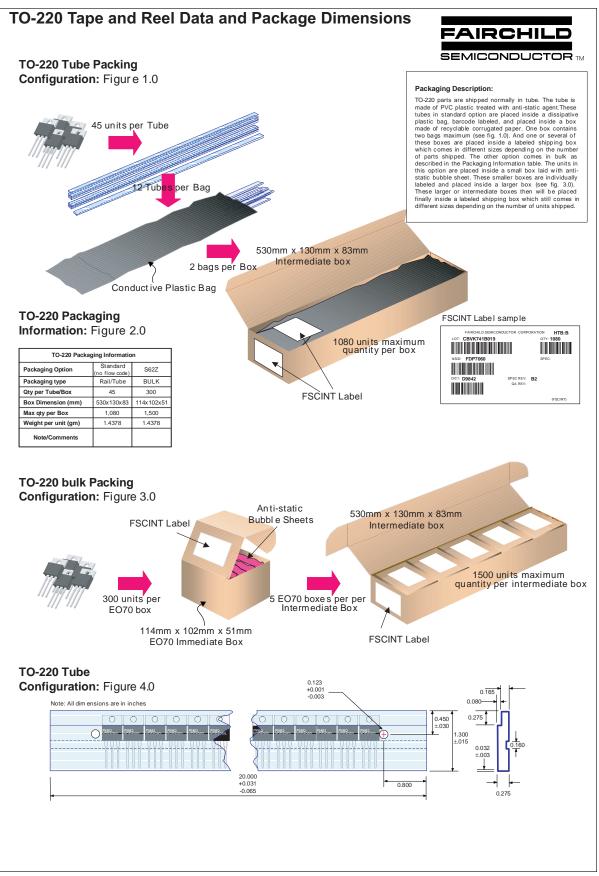
Note: 1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.



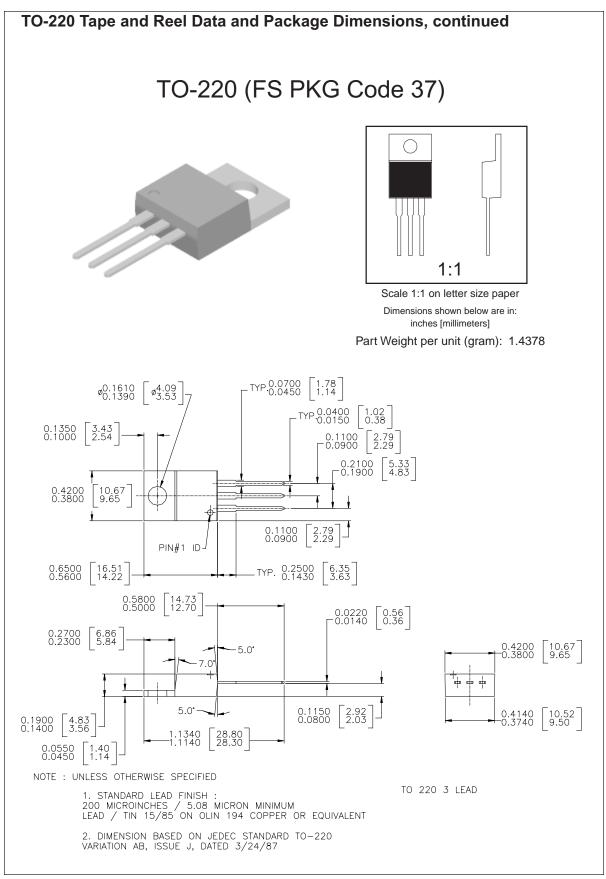


NDP6060 Rev. B1 / NDB6060 Rev. C

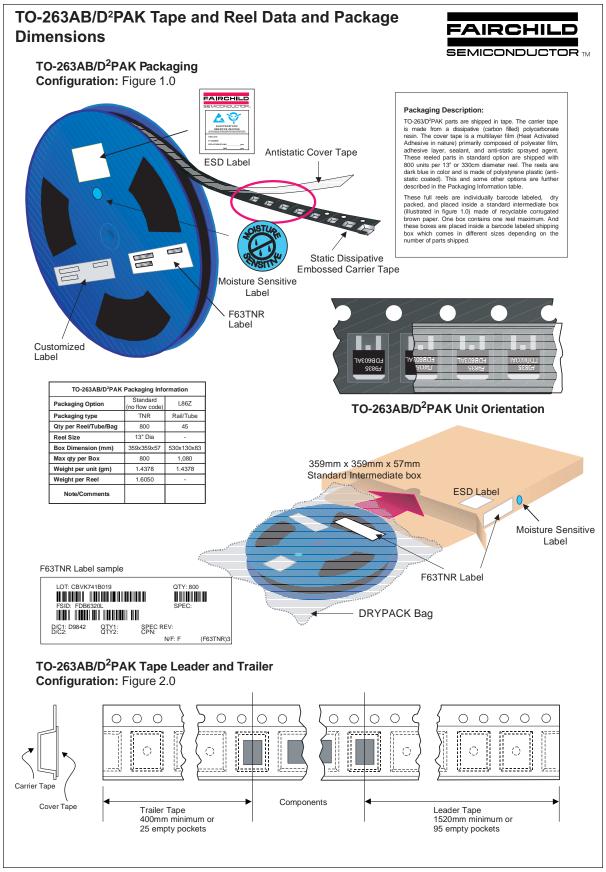




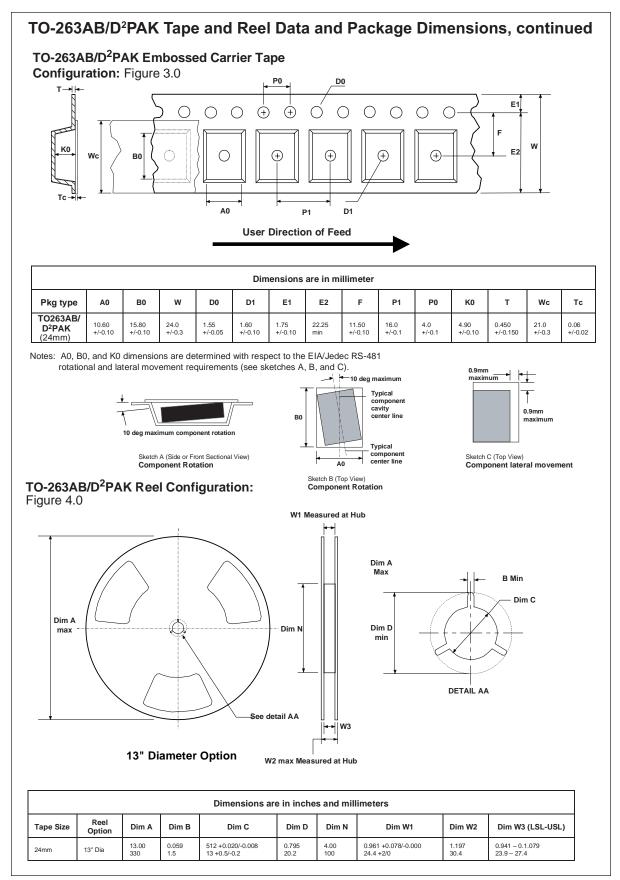
August 1999, Rev. B

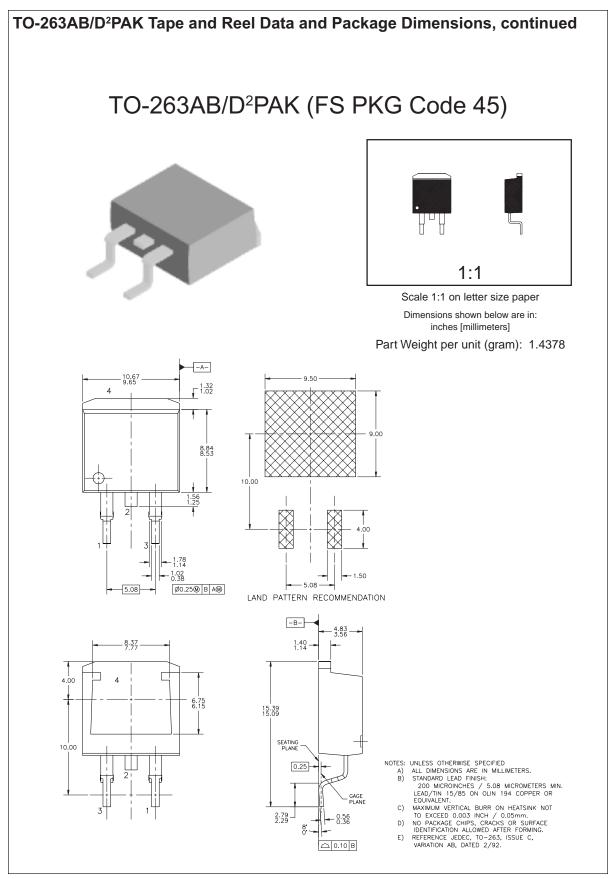


September 1998, Rev. A



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